IN THE SPECIFICATION:

On page 1, immediately after the title, please insert the following paragraph and heading as follows:

This specification for the instant application should be granted the priority date of December 23, 2002, the filing date of the corresponding German patent application 102 60 672.2 as well as the priority date of November 28, 2003, the filing date of the corresponding International patent application PCT/EP2003/013388.

Background of the Invention.

On page 3, line 14, please insert the following heading:

--Summary of the Invention--

On page 15, before line 1, please insert the following heading:

--Brief Description of the Drawings--

On page 16, line 18, please insert the following heading:

--Description of Specific Embodiments--.

On page 25, line 20 through page 26, line 5, please amend this paragraph as follows:

In the position shown in Fig. 3a, the semiconductor wafer 14 is supported essentially by the second ultrasonic electrodes 18 and is centered relative to them. If the second ultrasonic electrodes 18 are in the position shown in Fig. 3b, the semiconductor wafer 14 is supported exclusively by the ~~second~~ first ultrasonic electrode 16. By means of the lateral movement of the ultrasonic electrodes 18, the spacing between the wafer 14 and the first ultrasonic electrode 16 can thus be altered, whereby it is possible at any point in time to also exert a support force upon the wafer 14 via the first ultrasonic electrode 16 if the first ultrasonic electrode 16 is operated in the remote field.

On page 29, line 13, through page 30, line 12, please amend this paragraph as follows:

Fig. 7 again shows a cross-sectional illustration of a rapid heating unit 1 having a housing

3 and upper and lower banks of lamps 4, 5. Upper and lower quartz windows 7, 8 are again provided for the formation of a process chamber 10. However, instead of an ultrasonic electrode arrangement 13 that is comprised of at least two separate ultrasonic electrodes, pursuant to Fig. 7 only a single ultrasonic electrode 20 is provided for the support of a wafer 14 in the process chamber 10. The ultrasonic electrode 20, which is shown enlarged in Fig. 8, has a first, upwardly facing ultrasonic radiation surface 21 that has a peripheral shape corresponding to the wafer 14. Adjoining this planar radiation surface ~~20~~ 21 radially outwardly is a second ultrasonic radiation surface 22 that is angled relative thereto. The angle between the planar radiation surface 21 and the angled radiation surface 22 is preferably between 0.5 and 10°, although a larger angle is illustrated in Fig. 8. The ultrasonic radiation surfaces 21, 22 can be controlled either together or also separately by a suitable control unit. In contrast to the preceding embodiments, the planar ultrasonic radiation surface 21, and the ultrasonic radiation surface 22 that is angled relative thereto, are stationary relative to one another during the entire operation of the apparatus. A change in spacing between the wafer 14 and the planar ultrasonic radiation surface 21 is effected exclusively via an appropriate control of the respective ultrasonic radiation surfaces and an appropriate switching between a remote field and short-range field operation.

On page 34, after line 20, please insert the following two new paragraphs:

--The specification incorporates by reference the disclosure of German priority document 102 60 672.2 filed December 23, 2002 and PCT/EP2003/013388 filed November 28, 2003.

The present invention is, of course, in no way restricted to the specific disclosure of the specification and drawings, but also encompasses any modifications within the scope of the appended claims.—

In addition, please add the attached abstract to the specifcation: